

4.5V Drive Nch MOSFET

RMW200N03

Structure

Silicon N-channel MOSFET

● Features

- 1) High Power package(PSOP8).
- 2) High-speed switching, Low On-resistance.
- 3) Low voltage drive(4.5V drive).

Application

Switching

Packaging specifications

Type	Package	Taping	
	Code	TB	
	Basic ordering unit (pieces)	2500	
RMW200N03		0	

● Absolute maximum ratings (Ta = 25°C)

Parar	Symbol	Limits	Unit	
Drain-source voltage		V_{DSS}	30	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	Continuous	I _D	±20	Α
	Pulsed	I _{DP} *1	±80	Α
Source current (Body Diode)	Continuous	I _S	2.5	Α
	Pulsed	I _{SP} *1	80	Α
Power dissipation		P _D *2	3.0	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

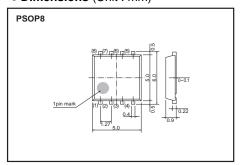
^{*1} Pw≤10µs, Duty cycle≤1%

• Thermal resistance

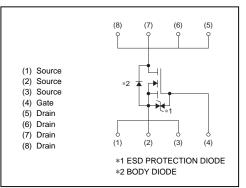
Parameter	Symbol	Limits	Unit
Channel to Ambient	Rth (ch-a)*	41.7	°C/W

^{*} MOUNTED ON 40mm × 40mm Cu BOARD

Dimensions (Unit : mm)



Inner circuit



^{*2} MOUNTED ON 40mm×40mm Cu BOARD

● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	1	-	±10	μA	$V_{GS}=\pm20V$, $V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	30	-	-	٧	I _D =1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	1	-	1	μA	V_{DS} =30V, V_{GS} =0V
Gate threshold voltage	V _{GS (th)}	1.0	-	2.5	V	V_{DS} =10V, I_{D} =1mA
Static drain-source on-state	R _{DS (on)} *	ı	3.0	4.2	mΩ	I _D =20A, V _{GS} =10V
resistance	DS (on)	ı	4.0	5.6		I _D =20A, V _{GS} =4.5V
Forward transfer admittance	IY _{fs} f*	20	-	-	S	I _D =20A, V _{DS} =10V
Input capacitance	C _{iss}	ı	1780	-	pF	V _{DS} =15V
Output capacitance	C _{oss}	1	580	-	рF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	ı	210	-	pF	f=1MHz
Turn-on delay time	t _{d(on)} *	-	18	-	ns	I _D =10A, V _{DD} ≒15V
Rise time	t _r *	1	50	-	ns	V _{GS} =10V
Turn-off delay time	t _{d(off)} *	ı	60	-	ns	$R_L=1.5\Omega$
Fall time	t _f *	ı	20	-	ns	$R_G=10\Omega$
Total gate charge	Q _g *	-	29	-	nC	I _D =20A, V _{DD} ≒15V
Gate-source charge	Q _{gs} *	-	5.7	-	nC	V _{GS} =10V
Gate-drain charge	Q _{gd} *	-	5.5	-	nC	

^{*}Pulsed

●Body diode characteristics (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward Voltage	V _{SD} *	-	-	1.2	V	I _s =2.5A, V _{GS} =0V

^{*}Pulsed

●Electrical characteristic curves (Ta=25°C)

Fig.1 Typical Output Characteristics(I)

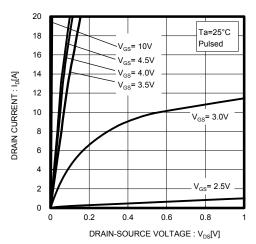


Fig.3 Typical Transfer Characteristics

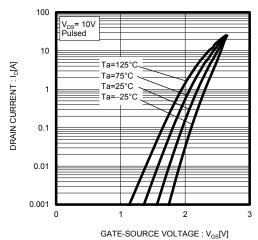


Fig.5 Static Drain-Source On-State

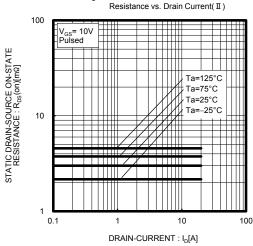


Fig.2 Typical Output Characteristics(II)

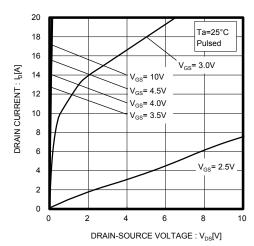


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(I)

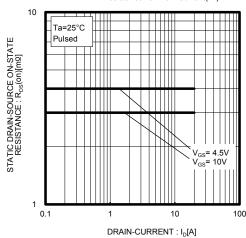
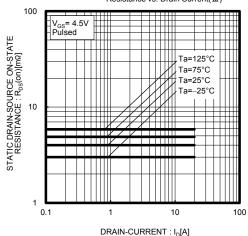
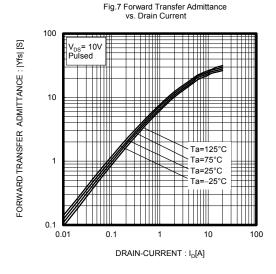
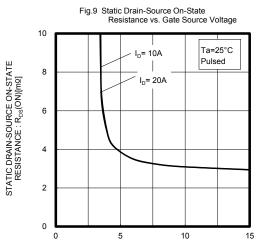
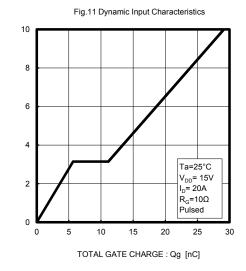


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(Ⅲ)



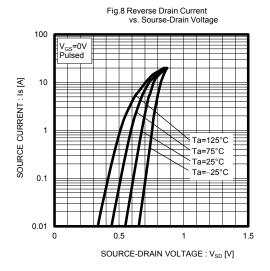


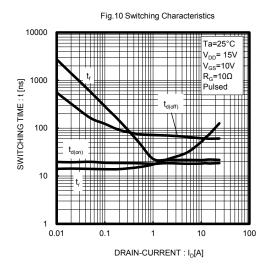




GATE-SOURCE VOLTAGE : V_{GS} [V]

GATE-SOURCE VOLTAGE : $V_{GS}[V]$





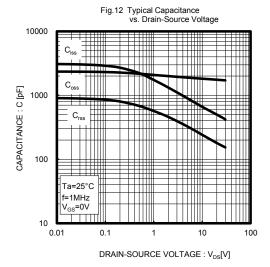


Fig.13 Maximum Safe Operating Aera

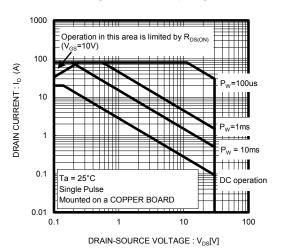
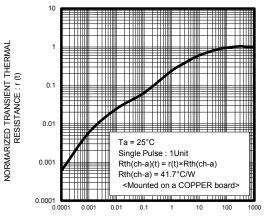


Fig.14 Normalized Transient Thermal Resistance vs. Pulse Width



PULSE WIDTH: Pw(s)

Measurement circuits

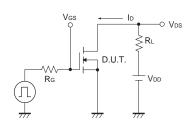


Fig.1-1 Switching Time Measurement Circuit

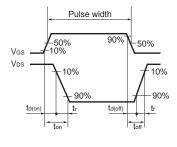


Fig.1-2 Switching Waveforms

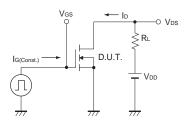


Fig.2-1 Gate Charge Measurement Circuit

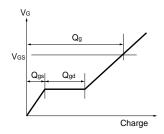


Fig.2-2 Gate Charge Waveform

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